

isc Silicon NPN Darlington Power Transistor

2SD1647

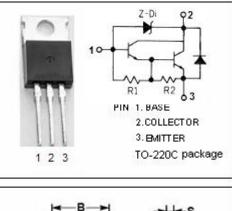
DESCRIPTION

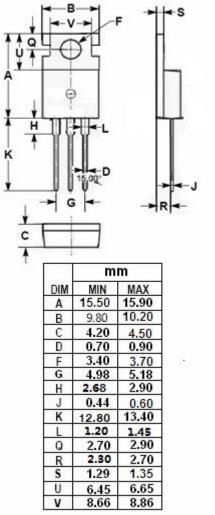
- · Low Collector-Emitter Saturation Voltage-: V_{CE(sat)} = 1.5V(Max)@ I_C= 1A
- High DC Current Gain
- : h_{FE}= 1000(Min) @I_C= 1.0A
- Low Saturation Voltage
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for general purpose amplifier and low frequency power Amp applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
PARAMETER VALUE		UNIT					
Collector-Base Voltage	50-70	V					
Collector-Emitter Voltage	50-70	V					
Emitter-Base Voltage	6	V					
Collector Current-Continuous	2	А					
Collector Current-Peak	3	А					
Collector Power Dissipation @ $T_c=25^{\circ}C$	25	w					
Junction Temperature	150	°C					
Storage Temperature Range	-55~150	°C					
	Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Collector Current-Continuous Collector Current-Peak Collector Power Dissipation @ Tc=25°C Junction Temperature	Collector-Base Voltage50-70Collector-Emitter Voltage50-70Emitter-Base Voltage6Collector Current-Continuous2Collector Current-Peak3Collector Power Dissipation @ Tc=25°C25Junction Temperature150					





isc website: <u>www.iscsemi.com</u>____

¹ *isc & iscsemi* is registered trademark



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 5mA, I _B = 0	50		70	V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 100 μ A, I _E = 0	50		70	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1A, I _B = 1mA			1.5	V
І _{сво}	Collector Cutoff Current	V _{CB} = 50V, I _E = 0			10	uA
I _{CEO}	Collector Cutoff Current	V _{CE} = 50V, I _B = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			3.0	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 2V	1000		10000	
Сов	Output Capacitance	I _E = 0 ; V _{CB} = 10V,f _{test} = 1MHz		25		pF

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